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(71) Applicant *(for all designated States except US)*: **INTEL CORPORATION** [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **DATTA, Suman** [IN/US]; 16659 Nw Talking Stick Way, Beaverton, OR 97006 (US). **BRASK, Justin, K.** [CA/US]; 12748 Nw Bayonne Lane, Portland, OR 97229 (US). **JIN, Been-yih** [US/US]; 12872 Sierra Court, Lake Oswego, OR 97035 (US). **KAVALIEROS, Jack, T.** [US/US]; 14620 Nw Belle Court, Portland, OR 97229 (US). **HUDAIT, Mantu, K.** [IN/US]; 12872 Sierra Court, Beaverton, OR 97006 (US).

(74) Agents: **VINCENT, Lester, J.** et al.; BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP, 12400 Wilshire Boulevard, 7th Floor, Los Angeles, CA 90025 (US).

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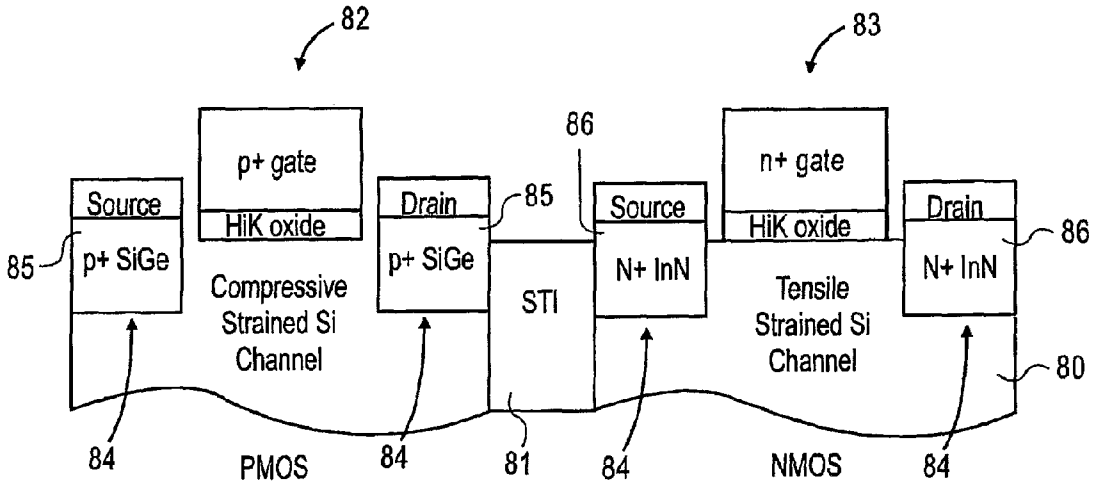
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(54) Title: A TENSILE STRAINED NMOS TRANSISTOR USING GROUP III-N SOURCE/DRAIN REGIONS



(57) Abstract: Enhancement mode transistors are described where a Group III-N compound is used in the source and drain regions to place tensile strain on the channel. The source and drain regions may be raised or embedded, and fabricated in conjunction with recessed or raised compression regions for p channel transistors.

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